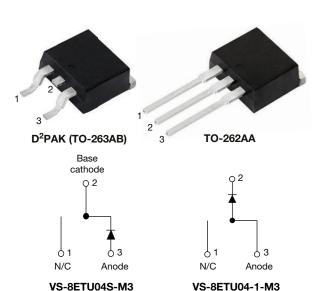


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HALOGEN

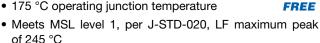
# Ultrafast Rectifier, 8 A FRED Pt®



PRIMARY CHARACTERISTICS						
I <sub>F(AV)</sub>	8 A					
$V_{R}$	400 V					
V <sub>F</sub> at I <sub>F</sub>	0.94 V					
t <sub>rr</sub> typ.	35 ns					
T <sub>J</sub> max.	175 °C					
Package	D <sup>2</sup> PAK (TO-263AB), TO-262AA					
Circuit configuration	Single					

#### **FEATURES**

- · Ultrafast recovery time
- · Low forward voltage drop
- · Low leakage current
- 175 °C operating junction temperature



• Material categorization: for definitions of compliance please see www.vishav.com/doc?99912

### **DESCRIPTION / APPLICATIONS**

Vishay Semiconductors FRED Pt® series are the state of the art ultrafast recovery rectifiers specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS				
Repetitive peak reverse voltage	$V_{RRM}$		400	V				
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>C</sub> = 155 °C	8					
Non-repetitive peak surge current	I <sub>FSM</sub>	T <sub>C</sub> = 25 °C	100	Α				
Repetitive peak forward current	I <sub>FRM</sub>		16					
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		-65 to +175	°C				

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	Ι <sub>R</sub> = 100 μΑ	400	-	-	.,		
Forward voltage	V	I <sub>F</sub> = 8 A	-	1.19	1.3	V		
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 8 A, T <sub>J</sub> = 150 °C	-	0.94	1.0			
Deviana laskaga ayuwant		$V_R = V_R$ rated	-	0.2	10			
Reverse leakage current	I <sub>R</sub>	T <sub>J</sub> = 150 °C, V <sub>R</sub> = V <sub>R</sub> rated	-	20	500	μA		
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 400 V	-	14	-	pF		
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8.0	-	nH		



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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS
		$I_F = 1.0 \text{ A}, dI_F/dt =$	$= 50 \text{ A/}\mu\text{s}, \text{ V}_{\text{R}} = 30 \text{ V}$	-	35	60	
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	43	-	ns A
		T <sub>J</sub> = 125 °C		-	67	-	
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 25 °C	I <sub>F</sub> = 8 A dI <sub>F</sub> /dt = 200 A/µs V <sub>B</sub> = 200 V	-	2.8	-	
		T <sub>J</sub> = 125 °C		-	6.3	-	
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 25 °C	VH = 200 V	-	60	-	
		T <sub>J</sub> = 125 °C		-	210	-	IIC

THERMAL - MECHANICAL SPI						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65	-	175	°C
Thermal resistance, junction-to-case	$R_{thJC}$		-	1.8	2.0	
Thermal resistance, junction-to-ambient	R <sub>thJA</sub>	Typical socket mount	-	-	50	°C/W
Thermal resistance, case-to-heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth, and greased	-	0.5	-	0,11
Mainh			-	2.0	-	g
Weight			-	0.07	-	OZ.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Mayling davida		Case style D <sup>2</sup> PAK (TO-263AB)	8ETU04S			
Marking device		Case style TO-262AA	8ETU04-1			

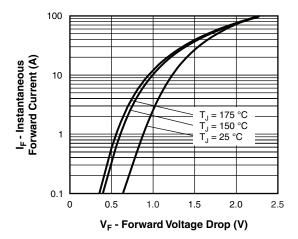


Fig. 1 - Typical Forward Voltage Drop Characteristics

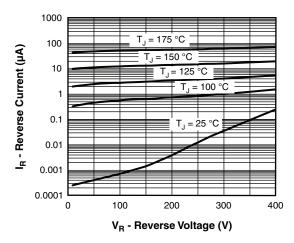


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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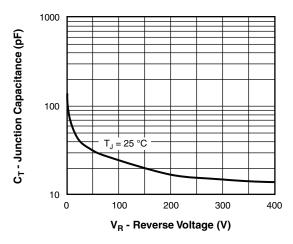


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

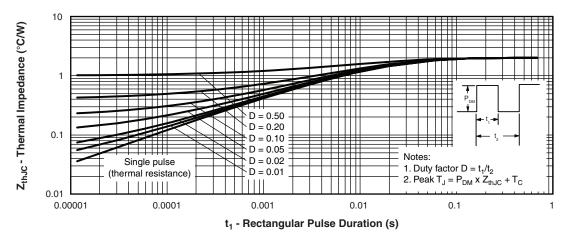


Fig. 4 - Maximum Thermal Impedance  $Z_{thJC}$  Characteristics

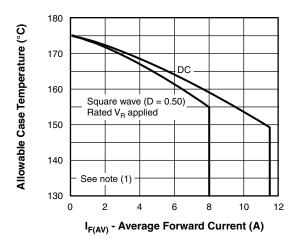


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

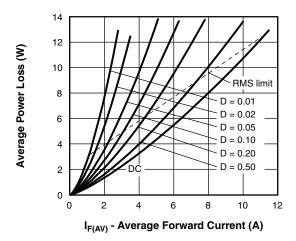


Fig. 6 - Forward Power Loss Characteristics



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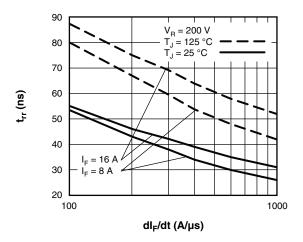


Fig. 7 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

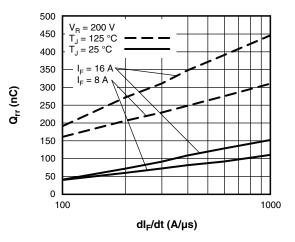
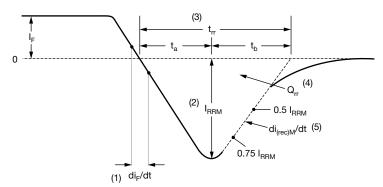


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt

#### Note

 $^{(1)}$  Formula used: T<sub>C</sub> = T<sub>J</sub> - (Pd + Pd<sub>REV</sub>) x R<sub>thJC</sub>; Pd = forward power loss = I<sub>F(AV)</sub> x V<sub>FM</sub> at (I<sub>F(AV)</sub>/D) (see fig. 6); Pd<sub>REV</sub> = inverse power loss = V<sub>R1</sub> x I<sub>R</sub> (1 - D); I<sub>R</sub> at V<sub>R1</sub> = rated V<sub>R</sub>



- (1) di<sub>F</sub>/dt rate of change of current through zero crossing
- (2) I<sub>RRM</sub> peak reverse recovery current
- (3)  $\rm t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $\rm I_F$  to point where a line passing through 0.75  $\rm I_{RRM}$  and 0.50  $\rm I_{RRM}$  extrapolated to zero current.
- (4)  $\mathbf{Q}_{rr}$  area under curve defined by  $\mathbf{t}_{rr}$  and  $\mathbf{I}_{\text{RRM}}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) di<sub>(rec)M</sub>/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

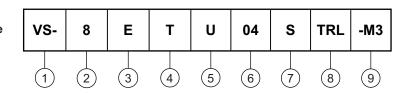
Fig. 9 - Reverse Recovery Waveform and Definitions

# VS-8ETU04S-M3, VS-8ETU04-1-M3

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### **ORDERING INFORMATION TABLE**

Device code



Vishay Semiconductors product

2 - Current rating (8 A)

3 - E = single

- T = TO-220, D<sup>2</sup>PAK (TO-263AB)

5 - U = ultrafast recovery

6 - Voltage rating (04 = 400 V)

7 - • S =  $D^2$ PAK (TO-263AB)

• -1 = TO-262AA

None = tube (50 pieces)

• TRL = tape and reel (left oriented, for D<sup>2</sup>PAK (TO-263AB) package)

• TRR = tape and reel (right oriented, for D<sup>2</sup>PAK (TO-263AB) package)

9 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)						
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION				
VS-8ETU04S-M3	50	Antistatic plastic tubes				
VS-8ETU04STRL-M3	800	13" diameter plastic tape and reel				
VS-8ETU04STRR-M3	800	13" diameter plastic tape and reel				
VS-8ETU04-1-M3	50	Antistatic plastic tubes				

LINKS TO RELATED DOCUMEN	TS	
Dimensions	D <sup>2</sup> PAK (TO-263AB)	www.vishay.com/doc?96164
Dimensions -	TO-262AA	www.vishay.com/doc?96165
Dart marking information	D <sup>2</sup> PAK (TO-263AB)	www.vishay.com/doc?95444
Part marking information -	TO-262AA	www.vishay.com/doc?95443
Packaging information	D <sup>2</sup> PAK (TO-263AB)	www.vishay.com/doc?96424



## Vishay Semiconductors

## D<sup>2</sup>PAK

#### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIM	ETERS	INC	HES	NOTES		SYMBOL	MILLIM	ETERS	INC	HES	NOTES
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOIES	123	STINIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

#### Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inches
- (7) Outline conforms to JEDEC® outline TO-263AB

Revision: 13-Jul-17 Document Number: 96164

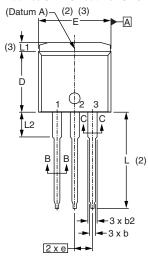


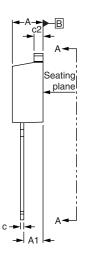
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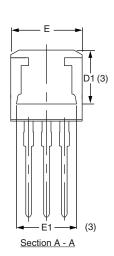
### **TO-262AA**

#### **DIMENSIONS** in millimeters and inches

#### Modified JEDEC® outline TO-262







**⊕** 0.010 **M** A**M** B

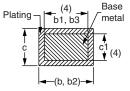
#### Lead assignments



**Diodes** 1. - Anode (two die)/open (one die)

2., 4. - Cathode

3. - Anode



Section B - B and C - C Scale: None

SYMBOL	MILLIM	IETERS	INC	INCHES			
	MIN.	MAX.	MIN.	MAX.	NOTES		
Α	4.06	4.83	0.160	0.190			
A1	2.03	3.02	0.080	0.119			
b	0.51	0.99	0.020	0.039			
b1	0.51	0.89	0.020	0.035	4		
b2	1.14	1.78	0.045	0.070			
b3	1.14	1.73	0.045	0.068	4		
С	0.38	0.74	0.015	0.029			
c1	0.38	0.58	0.015	0.023	4		
c2	1.14	1.65	0.045	0.065			
D	8.51	9.65	0.335	0.380	2		
D1	6.86	8.00	0.270	0.315	3		
Е	9.65	10.67	0.380	0.420	2, 3		
E1	7.90	8.80	0.311	0.346	3		
е	2.54	BSC	0.10	0 BSC			
L	13.46	14.10	0.530	0.555			
L1	-	1.65	-	0.065	3		
L2	3.56	3.71	0.140	0.146			

#### **Notes**

(4) Dimension b1 and c1 apply to base metal only

Controlling dimension: inches

<sup>(1)</sup> Dimensioning and tolerancing as per ASME Y14.5M-1994
(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

Thermal pad contour optional within dimension E, L1, D1 and E1

Outline conform to JEDEC® TO-262 except A1 (max.), b (min., max.), b1 (min.), b2 (max.), c (min.), c1(min.), c2 (max.), D (min.), E (max.), L1 (max.), L2 (min., max.)



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